Atsushi Masuda

List of Publications by Year
in descending order

230 papers	3,762 citations	136950 32 h-index	233421 45 g-index
231 all docs	231 docs citations	231 times ranked	1711 citing authors

#	Article	IF	Citations
1	Effect of temperature and pre-annealing on the potential-induced degradation of silicon heterojunction photovoltaic modules. Japanese Journal of Applied Physics, 2022, 61, SC1021.	1.5	3
2	Non-Destructive Measurement of Acetic Acid and Its Distribution in a Photovoltaic Module during Damp Heat Testing Using pH-Sensitive Fluorescent Dye Sensors. Sensors, 2022, 22, 2520.	3.8	4
3	Influence of light illumination on the potential-induced degradation of n-type interdigitated back-contact crystalline Si photovoltaic modules. Japanese Journal of Applied Physics, 2021, 60, SBBF08.	1.5	7
4	Fabrication of Tantalum-Doped Titanium-Oxide Electron-Selective Contacts with High Passivation Quality. ECS Journal of Solid State Science and Technology, 2021, 10, 045009.	1.8	2
5	Influence of Light Irradiation on Potential-Induced Degradation for Thin-Film Si Photovoltaic Modules. ECS Journal of Solid State Science and Technology, 2021, 10, 065018.	1.8	0
6	Effects of passivation configuration and emitter surface doping concentration on polarization-type potential-induced degradation in n-type crystalline-silicon photovoltaic modules. Solar Energy Materials and Solar Cells, 2021, 226, 111074.	6.2	16
7	Study on photo-degradation of inverted organic solar cells caused by generation of potential barrier between PEDOT:PSS and PBDB-Ts. Sustainable Energy and Fuels, 2021, 5, 3092-3096.	4.9	6
8	Potentialâ€Induced Degradation in Highâ€Efficiency nâ€Type Crystallineâ€Silicon Photovoltaic Modules: A Literature Review. Solar Rrl, 2021, 5, 2100708.	5.8	23
9	Characteristics change in organic photovoltaics by thermal recovery and photodegradation. Japanese Journal of Applied Physics, 2020, 59, SCCD04.	1.5	2
10	Effect of a SiO₂ film on the potential-induced degradation of n-type front-emitter crystalline Si photovoltaic modules. Japanese Journal of Applied Physics, 2020, 59, SCCD02.	1.5	13
11	Influence of emitter position of silicon heterojunction photovoltaic solar cell modules on their potential-induced degradation behaviors. Solar Energy Materials and Solar Cells, 2020, 216, 110716.	6.2	16
12	Potentialâ€induced degradation in photovoltaic modules composed of interdigitated back contact solar cells in photovoltaic systems under actual operating conditions. Progress in Photovoltaics: Research and Applications, 2020, 28, 1322-1332.	8.1	13
13	A scanning nonlinear dielectric microscopic investigation of potential-induced degradation in monocrystalline silicon solar cells. Applied Physics Letters, 2020, 116, 182107.	3.3	1
14	A single-phase brookite TiO₂ nanoparticle bridge enhances the stability of perovskite solar cells. Sustainable Energy and Fuels, 2020, 4, 2009-2017.	4.9	25
15	Elucidating the mechanism of potential induced degradation delay effect by ultraviolet light irradiation for p-type crystalline silicon solar cells. Solar Energy, 2020, 199, 55-62.	6.1	15
16	Influence of hygrothermal stress on potential-induced degradation for homojunction and heterojunction crystalline Si photovoltaic modules. Japanese Journal of Applied Physics, 2020, 59, 076503.	1.5	10
17	Effect of a silicon nitride film on the potential-induced degradation of n-type front-emitter crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2020, 59, 104002.	1.5	11
18	Temperature coefficient of the characteristic values of the charge-accumulation-type potential-induced-degraded n-type mono-crystalline silicon photovoltaic cell. Japanese Journal of Applied Physics, 2020, 59, 051001.	1.5	0

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19	(Invited) Reliability Improvement and Remaining Issues on Photovoltaic Cells and Modules. ECS Meeting Abstracts, 2020, MA2020-02, 1846-1846.	0.0	0
20	Women in physics in Japan. AIP Conference Proceedings, 2019, , .	0.4	1
21	Japanese women researchers: Are they active? â€" Trends in numbers of members in JSAP. AIP Conference Proceedings, 2019, , .	0.4	0
22	Actions for gender equality in the Japan society of applied physics. AIP Conference Proceedings, 2019, , .	0.4	0
23	Temperature dependence of potential-induced degraded p-type mono-crystalline silicon photovoltaic cell characteristics. Japanese Journal of Applied Physics, 2019, 58, 101005.	1.5	3
24	Output power behavior of passivated emitter and rear cell photovoltaic modules during early installation stage: influence of light-induced degradation. Japanese Journal of Applied Physics, 2019, 58, 106510.	1.5	3
25	Universal explanation for degradation by charge accumulation in crystalline Si photovoltaic modules with application of high voltage. Applied Physics Express, 2019, 12, 101003.	2.4	11
26	Influence of backsheet materials on potential-induced degradation in n-type crystalline-silicon photovoltaic cell modules. Japanese Journal of Applied Physics, 2019, 58, 120901.	1.5	3
27	Effect of additives in electrode paste of p-type crystalline Si solar cells on potential-induced degradation. Solar Energy, 2019, 188, 1292-1297.	6.1	10
28	Influence of sodium on the potential-induced degradation for n-type crystalline silicon photovoltaic modules. Applied Physics Express, 2019, 12, 064004.	2.4	17
29	Similarity of potential-induced degradation in superstrate-type thin-film CdTe and Si photovoltaic modules. Japanese Journal of Applied Physics, 2019, 58, SBBF07.	1.5	9
30	Investigation of UV and hygrothermal stress on back side of rack-mounted photovoltaic modules. Renewable Energy Focus, 2019, 29, 107-113.	4.5	4
31	Investigation of the power generation of organic photovoltaic modules connected to the power grid for more than three years. Japanese Journal of Applied Physics, 2019, 58, 052001.	1.5	7
32	Corrosion-Induced AC Impedance Elevation in Front Electrodes of Crystalline Silicon Photovoltaic Cells Within Field-Aged Photovoltaic Modules. IEEE Journal of Photovoltaics, 2019, 9, 741-751.	2.5	11
33	Corrections to â€œCorrosion-Induced AC Impedance Elevation in Front Electrodes of Crystalline Silicon Photovoltaic Cells Within Field-Aged Photovoltaic Modulesâ€•[May 19 741-751]. IEEE Journal of Photovoltaics, 2019, 9, 1154-1154.	2.5	4
34	Roles of SiNx in Potential-induced Degradation for p-type Crystalline Si Photovoltaic Modules. , 2019, , .		0
35	Durable crystalline Si photovoltaic modules based on silicone-sheet encapsulants. Japanese Journal of Applied Physics, 2018, 57, 027101.	1.5	18
36	Bending cyclic load test for crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 02CE05.	1.5	9

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37	Comprehensive study of potentialâ€induced degradation in silicon heterojunction photovoltaic cell modules. Progress in Photovoltaics: Research and Applications, 2018, 26, 697-708.	8.1	30
38	Multistage performance deterioration in n-type crystalline silicon photovoltaic modules undergoing potential-induced degradation. Microelectronics Reliability, 2018, 84, 127-133.	1.7	29
39	Detection of acetic acid produced in photovoltaic modules based on tin film corrosion during damp heat test. Japanese Journal of Applied Physics, 2018, 57, 08RG16.	1.5	7
40	Sodium distribution at the surface of silicon nitride film after potential-induced degradation test and recovery test of photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 08RG05.	1.5	5
41	Exploring suitable damp heat and potential induced degradation test procedures for Cu(In,Ga)(S,Se) photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 08RG02.	1.5	12
42	Overall analysis of change in power generation with outdoor exposure of photovoltaic modules installed at AIST Kyushu Center. Japanese Journal of Applied Physics, 2018, 57, 08RG04.	1.5	7
43	Soiling by volcanic ash fall on photovoltaic modules and effects of hydrophilic coating on module cover glass. Japanese Journal of Applied Physics, 2018, 57, 08RG06.	1.5	1
44	Comparison between Estimated and Actual Power Generation Amounts of Photovoltaic Modules at Tosu City in Japan. , 2018, , .		0
45	Effect of barrier property of backsheet on degradation of crystalline silicon photovoltaic modules under combined acceleration test composed of UV irradiation and subsequent damp-heat stress. Japanese Journal of Applied Physics, 2018, 57, 127101.	1.5	7
46	Origin of Na causing potential-induced degradation for p-type crystalline Si photovoltaic modules. AIP Advances, 2018, 8, .	1.3	6
47	Rapid progression and subsequent saturation of polarization-type potential-induced degradation of n-type front-emitter crystalline-silicon photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 122301.	1.5	30
48	Annual Degradation Rates of Recent c-Si PV Modules under Subtropical Coastal Climate Conditions. , 2018, , .		4
49	Potential-induced degradation of n-type crystalline Si photovoltaic modules in practical outdoor systems. Japanese Journal of Applied Physics, 2018, 57, 117102.	1.5	8
50	Accelerated Outdoor PID Testing of CIGS Modules and Comparison with Indoor PID Tests. , 2018, , .		3
51	Effect of light irradiation during potential-induced degradation tests for p-type crystalline Si photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 08RG13.	1.5	11
52	Reliability and long term durability of bifacial photovoltaic modules using transparent backsheet. Japanese Journal of Applied Physics, 2018, 57, 08RG15.	1.5	12
53	Temperature dependence measurements and performance analyses of high-efficiency interdigitated back-contact, passivated emitter and rear cell, and silicon heterojunction photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 08RG18.	1.5	14
54	Guiding principle for crystalline Si photovoltaic modules with high tolerance to acetic acid. Japanese Journal of Applied Physics, 2018, 57, 04FS06.	1.5	9

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55	Effect of bias voltage application on potential-induced degradation for crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 08RG01.	1.5	5
56	Performance degradation due to outdoor exposure and seasonal variation in amorphous silicon photovoltaic modules. Thin Solid Films, 2018, 661, 116-121.	1.8	13
57	Accurate measurement and estimation of solar cell temperature in photovoltaic module operating in real environmental conditions. Japanese Journal of Applied Physics, 2018, 57, 08RG08.	1.5	13
58	Lamination-interface-dependent deacetylation of ethylene vinyl acetate encapsulant in crystalline Si photovoltaic modules evaluated by positron annihilation lifetime spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 082301.	1.5	5
59	Localization and Characterization of a Degraded Site in Crystalline Silicon Photovoltaic Cells Exposed to Acetic Acid Vapor. IEEE Journal of Photovoltaics, 2018, 8, 997-1004.	2.5	19
60	Influence of surface structure of n-type single-crystalline Si solar cells on potential-induced degradation. Solar Energy Materials and Solar Cells, 2017, 166, 132-139.	6.2	32
61	Reduction in the short-circuit current density of silicon heterojunction photovoltaic modules subjected to potential-induced degradation tests. Solar Energy Materials and Solar Cells, 2017, 161, 439-443.	6.2	34
62	Causes of Degradation Identified by the Extended Thermal Cycling Test on Commercially Available Crystalline Silicon Photovoltaic Modules. IEEE Journal of Photovoltaics, 2017, 7, 1511-1518.	2.5	33
63	Annual degradation rates of recent crystalline silicon photovoltaic modules. Progress in Photovoltaics: Research and Applications, 2017, 25, 953-967.	8.1	95
64	Potential-induced degradation of thin-film Si photovoltaic modules. Japanese Journal of Applied Physics, 2017, 56, 04CS04.	1.5	12
65	Development of a practical method of estimating electric power from various photovoltaic technologies with high precision. Japanese Journal of Applied Physics, 2017, 56, 08MD05.	1.5	5
66	Effect of light irradiation and forward bias during PID tests of CIGS PV modules. , 2017, , .		1
67	Time-dependent changes in copper indium gallium (di)selenide and cadmium telluride photovoltaic modules due to outdoor exposure. Japanese Journal of Applied Physics, 2017, 56, 08MD06.	1.5	3
68	Sequential and combined acceleration tests for crystalline Si photovoltaic modules. Japanese Journal of Applied Physics, 2016, 55, 04ES10.	1.5	21
69	Behavior of the potential-induced degradation of photovoltaic modules fabricated using flat mono-crystalline silicon cells with different surface orientations. Japanese Journal of Applied Physics, 2016, 55, 04ES14.	1.5	7
70	Degradation of encapsulants for photovoltaic modules made of ethylene vinyl acetate studied by positron annihilation lifetime spectroscopy. Japanese Journal of Applied Physics, 2016, 55, 102302.	1.5	5
71	Potential-induced degradation behavior of n-type single-crystalline silicon photovoltaic modules with a rear-side emitter. , 2016, , .		4
72	Proposed new damp heat test standards for commercial CIGS modules with bias application or light irradiation. Proceedings of SPIE, 2016, , .	0.8	3

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73	Direct evidence for pn junction without degradation in crystalline Si photovoltaic modules under hygrothermal stresses. , 2016, , .		4
74	Electrical detection of gap formation underneath finger electrodes on c-Si PV cells exposed to acetic acid vapor under hygrothermal conditions. , 2016, , .		22
75	Microscopic aspects of potential-induced degradation phenomena and their recovery processes for p-type crystalline Si photovoltaic modules. Current Applied Physics, 2016, 16, 1659-1665.	2.4	35
76	Multi angle laser light scattering evaluation of field exposed thermoplastic photovoltaic encapsulant materials. Energy Science and Engineering, 2016, 4, 40-51.	4.0	13
77	Progression of rapid potential-induced degradation of n-type single-crystalline silicon photovoltaic modules. Applied Physics Express, 2016, 9, 112301.	2.4	32
78	Effects of UV on power degradation of photovoltaic modules in combined acceleration tests. Japanese Journal of Applied Physics, 2016, 55, 052301.	1.5	23
79	Issues and Solutions Concerned in the Coefficient of Thermal Expansion on Photovoltaic Modules. Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan, 2016, 67, 146-148.	0.2	0
80	Acceleration of degradation by highly accelerated stress test and air-included highly accelerated stress test in crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2016, 55, 022302.	1.5	14
81	Changes in the current densityâ€“voltage and external quantum efficiency characteristics of n-type single-crystalline silicon photovoltaic modules with a rear-side emitter undergoing potential-induced degradation. Solar Energy Materials and Solar Cells, 2016, 151, 113-119.	6.2	50
82	Consideration on Na diffusion and recovery phenomena in potential-induced degradation for crystalline Si photovoltaic modules. Japanese Journal of Applied Physics, 2016, 55, 02BF10.	1.5	21
83	Field testing of thermoplastic encapsulants in highâ€temperature installations. Energy Science and Engineering, 2015, 3, 565-580.	4.0	29
84	Acceleration of potential-induced degradation by salt-mist preconditioning in crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2015, 54, 08KG08.	1.5	22
85	Plasma-enhanced chemical-vapor deposition of silicon nitride film for high resistance to potential-induced degradation. Japanese Journal of Applied Physics, 2015, 54, 08KD12.	1.5	16
86	Degradation by acetic acid for crystalline Si photovoltaic modules. Japanese Journal of Applied Physics, 2015, 54, 04DR04.	1.5	43
87	Effects of light illumination during damp/dry heat tests on a flexible thin film photovoltaic module. Proceedings of SPIE, 2015, , .	0.8	2
88	Potential-induced degradation of Cu(In,Ga)Se₂photovoltaic modules. Japanese Journal of Applied Physics, 2015, 54, 08KC13.	1.5	64
89	Crystalline Si photovoltaic modules functionalized by a thin polyethylene film against potential and damp-heat-induced degradation. RSC Advances, 2015, 5, 15017-15023.	3.6	32
90	Potential-induced degradation in photovoltaic modules based on n-type single crystalline Si solar cells. Solar Energy Materials and Solar Cells, 2015, 140, 361-365.	6.2	88

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91	Module composition for reliability test of organic photovoltaics. Japanese Journal of Applied Physics, 2015, 54, 08KF07.	1.5	1
92	Relationship between cross-linking conditions of ethylene vinyl acetate and potential induced degradation for crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2015, 54, 08KG01.	1.5	35
93	Development of a pH sensor based on a nanostructured filter adding pH-sensitive fluorescent dye for detecting acetic acid in photovoltaic modules. Japanese Journal of Applied Physics, 2015, 54, 08KG07.	1.5	8
94	Novel lighter weight crystalline silicon photovoltaic module using acrylic-film as a cover sheet. Japanese Journal of Applied Physics, 2014, 53, 092302.	1.5	41
95	Detection of acid moisture in photovoltaic modules using a dual wavelength pH-sensitive fluorescent dye. Japanese Journal of Applied Physics, 2014, 53, 04ER18.	1.5	9
96	Crystalline Si photovoltaic modules based on TiO₂-coated cover glass against potential-induced degradation. RSC Advances, 2014, 4, 44291-44295.	3.6	57
97	Investigation on antireflection coating for high resistance to potential-induced degradation. Japanese Journal of Applied Physics, 2014, 53, 03CE01.	1.5	29
98	Microscopic Degradation Mechanisms in Silicon Photovoltaic Module under Long-Term Environmental Exposure. Japanese Journal of Applied Physics, 2012, 51, 10NF07.	1.5	17
99	Early Failure Detection of Interconnection with Rapid Thermal Cycling in Photovoltaic Modules. Japanese Journal of Applied Physics, 2012, 51, 10NF13.	1.5	6
100	Measuring Method of Moisture Ingress into Photovoltaic Modules. Japanese Journal of Applied Physics, 2012, 51, 10NF12.	1.5	5
101	Failure Assessments for Outside-Exposed Photovoltaic Modules. Japanese Journal of Applied Physics, 2012, 51, 10NF04.	1.5	3
102	Recent Situation and Future Prospects of Photovoltaic Industries and Technologies. Journal of the Vacuum Society of Japan, 2012, 55, 520-528.	0.3	0
103	Microscopic Degradation Mechanisms in Silicon Photovoltaic Module under Long-Term Environmental Exposure. Japanese Journal of Applied Physics, 2012, 51, 10NF07.	1.5	15
104	Measuring Method of Moisture Ingress into Photovoltaic Modules. Japanese Journal of Applied Physics, 2012, 51, 10NF12.	1.5	8
105	Early Failure Detection of Interconnection with Rapid Thermal Cycling in Photovoltaic Modules. Japanese Journal of Applied Physics, 2012, 51, 10NF13.	1.5	6
106	Recent Situation and Future Prospects of Photovoltaics. Nippon Gomu Kyokaishi, 2011, 84, 153-160.	0.0	1
107	Study on silicon-slicing technique using plasma-etching processing. Solar Energy Materials and Solar Cells, 2009, 93, 789-791.	6.2	11
108	Investigation on the crystal growth process of spherical Si single crystals by melting. Journal of Crystal Growth, 2009, 311, 4116-4122.	1.5	14

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109	Improvement of the uniformity in electronic properties of AZO films using an rf magnetron sputtering with a mesh grid electrode. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 148, 26-29.	3.5	12
110	Coverage properties of SiNx films prepared by catalytic chemical vapor deposition on trenched substrates below 80ÂÂ°C. Thin Solid Films, 2008, 516, 3000-3004.	1.8	3
111	Cat-CVD SiN passivation films for OLEDs and packaging. Thin Solid Films, 2008, 516, 553-557.	1.8	22
112	Epitaxial Growth of SiC on Silicon on Insulator Substrates with Ultrathin Top Si Layer by Hot-Mesh Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2008, 47, 569-572.	1.5	6
113	Formation of Low-Defect-Concentration Polycrystalline Silicon Films by Thermal Plasma Jet Crystallization Technique. Japanese Journal of Applied Physics, 2008, 47, 6949-6952.	1.5	17
114	Investigating minority-carrier lifetime in small spherical Si using microwave photoconductance decay. Journal of Applied Physics, 2008, 103, 104909.	2.5	6
115	Improvement of the Production Yield of Spherical Si by Optimization of the Seeding Technique in the Dropping Method. Japanese Journal of Applied Physics, 2007, 46, 5695-5700.	1.5	8
116	Defect Reduction in Polycrystalline Silicon Thin Films by Heat Treatment with High-Pressure H2O Vapor. Japanese Journal of Applied Physics, 2007, 46, 1286-1289.	1.5	22
117	Characterization of spherical Si by photoluminescence measurement. Journal of Applied Physics, 2007, 101, 103530.	2.5	8
118	Seeding method with silicon powder for the formation of silicon spheres in the drop method. Journal of Applied Physics, 2007, 101, 093505.	2.5	18
119	A concentrator module of spherical Si solar cell. Solar Energy Materials and Solar Cells, 2007, 91, 1805-1810.	6.2	23
120	Mass-Spectrometric Studies of Catalytic Chemical Vapor Deposition Processes of Organic Silicon Compounds Containing Nitrogen. Japanese Journal of Applied Physics, 2006, 45, 961-966.	1.5	18
121	Improvement of Crystallinity and Solar Cell Efficiency of Spherical Silicon by Seeding Crystallization Techniques. , 2006, , .		0
122	H2 dilution effect in the Cat-CVD processes of the SiH4/NH3 system. Thin Solid Films, 2006, 501, 31-34.	1.8	20
123	Systematic study on photoresist removal using hydrogen atoms generated on heated catalyzer. Thin Solid Films, 2006, 501, 326-328.	1.8	32
124	Present status and future feasibility for industrial implementation of Cat-CVD (Hot-Wire CVD) technology. Thin Solid Films, 2006, 501, 58-60.	1.8	33
125	High-rate deposition of SiNx films over 100 nm/min by Cat-CVD method at low temperatures below 80 Â°C. Thin Solid Films, 2006, 501, 55-57.	1.8	7
126	Various applications of silicon nitride by catalytic chemical vapor deposition for coating, passivation and insulating films. Thin Solid Films, 2006, 501, 149-153.	1.8	34

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127	Formation of highly moisture-resistive SiNx films on Si substrate by Cat-CVD at room temperature. Thin Solid Films, 2006, 501, 154-156.	1.8	6
128	Preparation of SiNx gate-insulating films for bottom-gate type TFTs by Cat-CVD method. Thin Solid Films, 2006, 501, 307-309.	1.8	1
129	Grain Enlargement of Polycrystalline Silicon by Multipulse Excimer Laser Annealing: Role of Hydrogen. Japanese Journal of Applied Physics, 2006, 45, 2726-2730.	1.5	18
130	Low-Temperature Deposition of Silicon Nitride Films by a Cat-CVD Technique-Gas-Phase Diagnoses and Evaluation of Film Properties-. Zairyo/Journal of the Society of Materials Science, Japan, 2006, 55, 142-147.	0.2	0
131	Preparation of Low-Stress SiNxFilms by Catalytic Chemical Vapor Deposition at Low Temperatures. Japanese Journal of Applied Physics, 2005, 44, 4098-4102.	1.5	12
132	Quantification of Gas-Phase H-Atom Number Density by Tungsten Phosphate Glass. Japanese Journal of Applied Physics, 2005, 44, 732-735.	1.5	28
133	Moisture-Resistive Properties of SiNxFilms Prepared by Catalytic Chemical Vapor Deposition below 100Â°C for Flexible Organic Light-Emitting Diode Displays. Japanese Journal of Applied Physics, 2005, 44, 1923-1927.	1.5	10
134	Improvement of Deposition Rate by Sandblasting of Tungsten Wire in Catalytic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2005, 44, 1943-1944.	1.5	0
135	Technique for the production, preservation, and transportation of H atoms in metal chambers for processings. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1728-1731.	2.1	21
136	Air-stable n-type carbon nanotube field-effect transistors with Si3N4 passivation films fabricated by catalytic chemical vapor deposition. Applied Physics Letters, 2005, 86, 113115.	3.3	91
137	Effect of Atomic Hydrogen on Preparation of Highly Moisture-Resistive SiNxFilms at Low Substrate Temperatures. Japanese Journal of Applied Physics, 2004, 43, L1546-L1548.	1.5	13
138	Correlation between O/Er Content Ratio and Photoluminescence Intensity of (Er, O)-Doped Hydrogenated Amorphous Si Thin Films Prepared by a Catalytic Chemical Vapor Deposition/Laser Ablation Hybrid Process. Japanese Journal of Applied Physics, 2004, 43, 4198-4201.	1.5	2
139	Highly Moisture-Resistive SiNxFilms Prepared by Catalytic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2004, 43, L1362-L1364.	1.5	20
140	Nitridation of Ultrathin SiO2 Layers in Metal-Ferroelectric-Insulator-Semiconductor Structures. Integrated Ferroelectrics, 2004, 68, 29-36.	0.7	1
141	Highly moisture-resistive silicon nitride films prepared by catalytic chemical vapor deposition and application to gallium arsenide field-effect transistors. Vacuum, 2004, 74, 525-529.	3.5	23
142	Study on change in SIMS intensities near the interface between silicon-nitride film and silicon substrate. Applied Surface Science, 2004, 231-232, 725-728.	6.1	4
143	Cat-CVD (hot-wire CVD): how different from PECVD in preparing amorphous silicon. Journal of Non-Crystalline Solids, 2004, 338-340, 19-26.	3.1	41
144	Catalytic decomposition of HCN on heated W surfaces to produce CN radicals. Journal of Non-Crystalline Solids, 2004, 338-340, 65-69.	3.1	11

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145	Catalytic Chemical Vapor Deposition of a-Si:H TFT. , 2004, , 377-394.		0
146	Development of Cat-CVD apparatus for 1-m-size large-area deposition. Thin Solid Films, 2003, 430, 58-62.	1.8	29
147	Fabrication of a-Si1â^'xCx:H thin films for solar cells by the Cat-CVD method using a carbon catalyzer. Thin Solid Films, 2003, 430, 170-173.	1.8	9
148	Deposition chemistry in the Cat-CVD processes of the SiH4/NH3 system. Thin Solid Films, 2003, 430, 24-27.	1.8	40
149	Recent progress of Cat-CVD research in Japanâ€"bridging between the first and second Cat-CVD conferences. Thin Solid Films, 2003, 430, 7-14.	1.8	38
150	Crystallization by excimer laser annealing for a-Si:H films with low hydrogen content prepared by Cat-CVD. Thin Solid Films, 2003, 430, 296-299.	1.8	17
151	Radical Species Formed by the Catalytic Decomposition of NH3on Heated W Surfaces. Japanese Journal of Applied Physics, 2003, 42, 5315-5321.	1.5	57
152	57.1: Invited Paper: Present Status of Cat-CVD as a New Fabrication Technology for Large Area Display. Digest of Technical Papers SID International Symposium, 2003, 34, 1504.	0.3	0
153	Properties of High Quality p-Type Micro-Crystalline-Si Prepared by Cat-CVD. Materials Research Society Symposia Proceedings, 2003, 762, 1321.	0.1	1
154	Properties of Phosphorus-Doped Polycrystalline Silicon Films Formed by Catalytic Chemical Vapor Deposition and Successive Rapid Thermal Annealing. , 2003, , 63-68.		0
155	Catalytic Chemical Vapor Deposition Recent Development and Future Prospects. Shinku/Journal of the Vacuum Society of Japan, 2003, 46, 92-97.	0.2	1
156	Low-Resistivity Phosphorus-Doped Polycrystalline Silicon Thin Films Formed by Catalytic Chemical Vapor Deposition and Successive Rapid Thermal Annealing. Japanese Journal of Applied Physics, 2002, 41, 501-506.	1.5	16
157	Effects of atomic hydrogen in gas phase on a-Si:H and poly-Si growth by catalytic CVD. Journal of Non-Crystalline Solids, 2002, 299-302, 9-13.	3.1	24
158	Direct detection of H atoms in the catalytic chemical vapor deposition of the SiH4/H2 system. Journal of Applied Physics, 2002, 91, 1650-1656.	2.5	156
159	Recent Progress in Industrial Applications of CAT-CVD (Hot-Wire Cvd). Materials Research Society Symposia Proceedings, 2002, 715, 1741.	0.1	7
160	In situ chamber cleaning using atomic H in catalytic-CVD apparatus for mass production of a-Si:H solar cells. Solar Energy Materials and Solar Cells, 2002, 74, 373-377.	6.2	9
161	Influence of atomic hydrogen on transparent conducting oxides during hydrogenated amorphous and microcrystalline Si preparation by catalytic chemical vapor deposition. Thin Solid Films, 2002, 411, 166-170.	1.8	13
162	What is the difference between catalytic CVD and plasma-enhanced CVD? Gas-phase kinetics and film properties. Vacuum, 2002, 66, 293-297.	3.5	5

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163	Development of Large-Area Uniform Deposition Technique on 1-m-Size Substrate by Catalytic Chemical Vapor Deposition.. Shinku/Journal of the Vacuum Society of Japan, 2002, 45, 123-126.	0.2	2
164	Title is missing!. Shinku/Journal of the Vacuum Society of Japan, 2002, 45, 727-732.	0.2	0
165	Properties of Large Grain-Size poly-Si Films by Catalytic Chemical Sputtering. Materials Research Society Symposia Proceedings, 2001, 664, 451.	0.1	5
166	Identification and gas phase kinetics of radical species in Cat-CVD processes of SiH4. Thin Solid Films, 2001, 395, 47-50.	1.8	56
167	Development of Cat-CVD apparatus â€" a method to control wafer temperatures under thermal influence of heated catalyzer. Thin Solid Films, 2001, 395, 71-74.	1.8	12
168	Photo-induced volume changes in a-Si:H films prepared by Cat-CVD method. Thin Solid Films, 2001, 395, 84-86.	1.8	6
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